

Amendments to the Specification:

Please replace the paragraph beginning at page 4, line 11 with the following re-written paragraph:

FIGS. [[6A-E]] 6A-F are cross-sectional views of a portion of a substrate at various stages of a processing method in accordance with an embodiment of the invention,

Please replace the paragraph beginning at page 10, line 26 with the following re-written paragraph:

With reference to FIG. 6C, a conformal thin film 36 of an opaque material is deposited to a thickness adequate for filling the undercut regions 32. With reference to FIG 6C, an anisotropic etch selective to at least the mask material layer 10 is performed to remove portions of layer 36 to leave behind spacers 32 that fill the undercut regions 34 and which are self-aligned to phase shift windows 14. With reference to FIGS. 6D and 6E, the handle substrate 12, containing the patterned masking film 10 and opaque features or spacers 32, is then bonded to the mask blank 20, and then the handle substrate 12 is removed, as shown in FIG. 6F, using methods as described above.